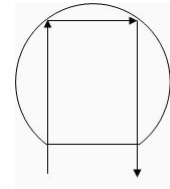


Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	650.00 +/- 12.50 $\mu$ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00 $\mu$ m	Guaranteed by Process
	7.0	Bow	<80.00 $\mu$ m	ADE to ASTM F534, 20%
	8.0	Warp	<80.00 $\mu$ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	500.00 +/- 10.00 $\mu$ m	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	0.001 - 1 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with IceMOS laser mark and oxide	Guaranteed by process
BuriedOxide	18.0	Oxide Type	Thermal	Wafer Vendor
	19.0	Oxide Thickness	2,000.00 +/- 150.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle wafer	Guaranteed by process
DeviceSilicon	21.0	Device Growth Method	FZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	150.00 +/- 2.00 $\mu$ m	FTIR, 100% 9-Pt (note3 and 4)
	24.0	Distance to device silicon edge from wafer edge	<2mm	Typical by process
	25.0	Device Doping Type	P	Wafer Vendor
	26.0	Device Dopant	Boron	Wafer Vendor
	27.0	Device Resistivity	>5000 Ohmcm	Wafer Vendor
	28.0	Buried Layer Implant	Species = Boron, Energy = 40 KeV, Dose = 5e14 at/cm2, Screen Ox = 240A	Ion Implant Vendor
	29.0	Voids	none	Wafer Vendor
	30.0	Scratches	0	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer
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Category	Parameter	Specification	Measurement Method
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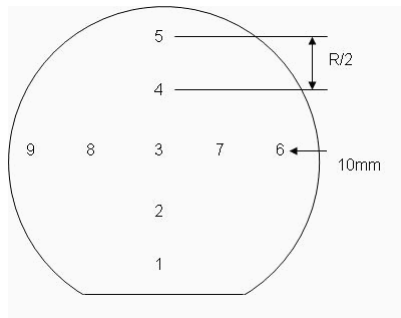
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information